



Probing with Heavy Ions the SET sensitivity of Linear Devices

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ONERA study under CNES contract



retour sur innovation

Goals and motivations

Probing LM124 with High LET ions

Comparing heavy ion probing with laser probing & mapping

Correlate heavy ion and laser data

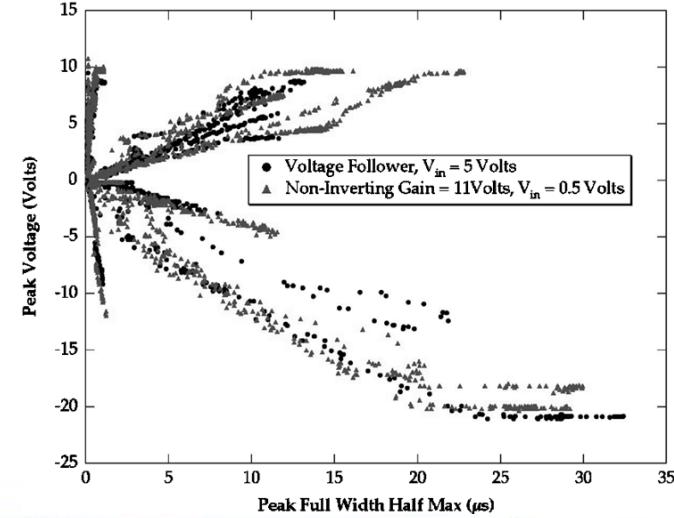
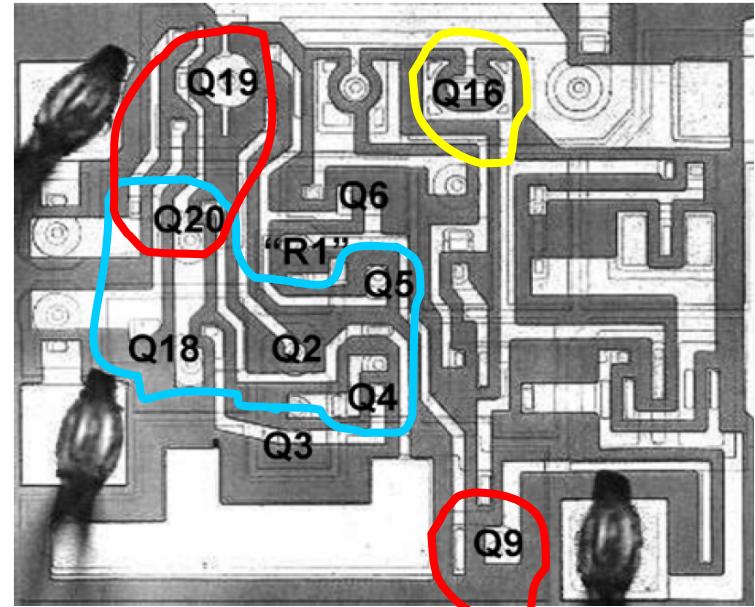
Validate the laser technique

Comparison with laser can help defining the most appropriate conditions for heavy ion testing

Help defining the appropriate methodology to be used for predicting SET rates (ex: SAC-D and JASON2 missions)

LM124 : 3 main families of SET events

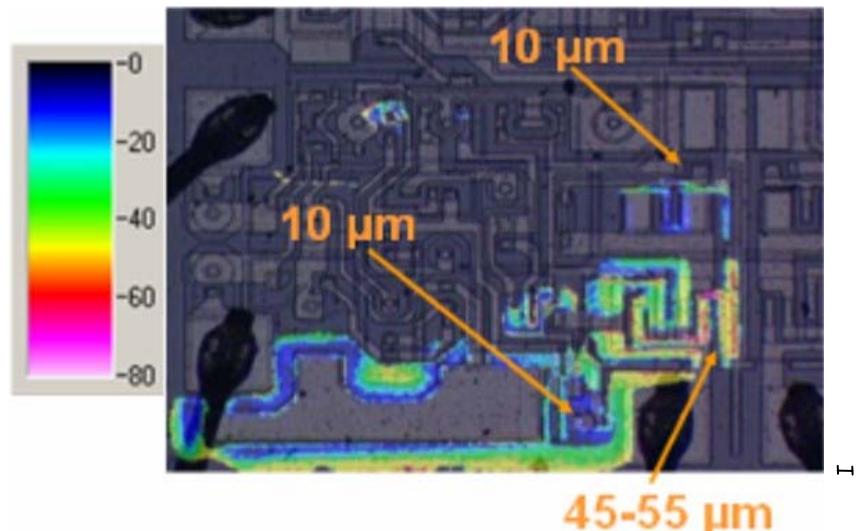
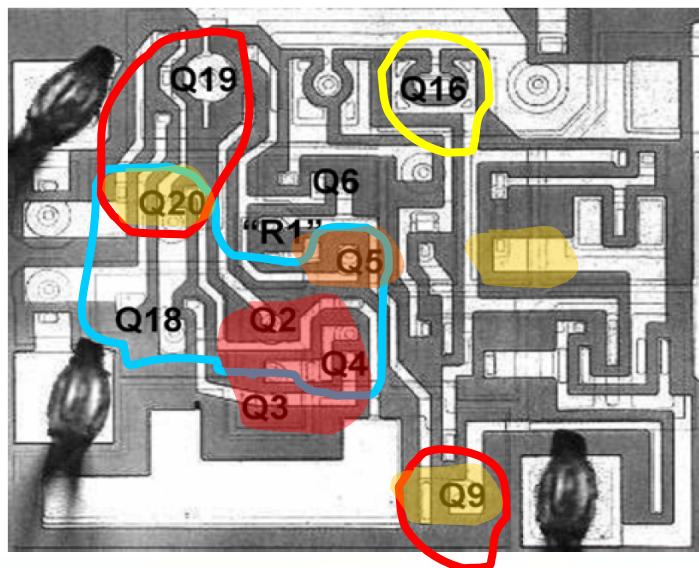
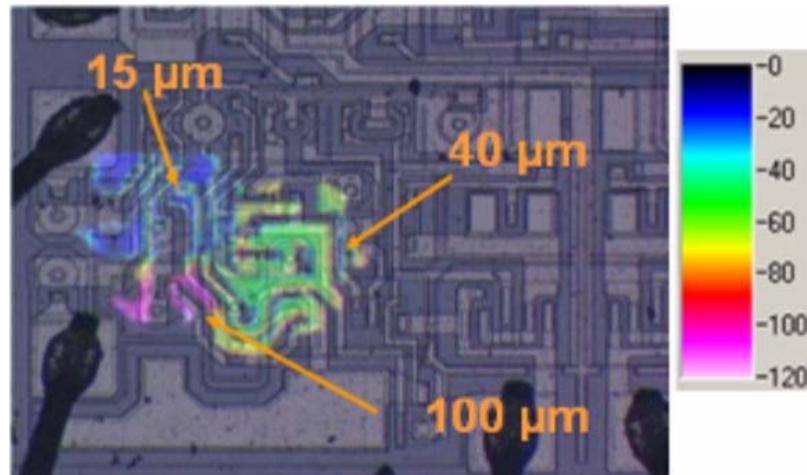
<i>SET type</i>	<i>Transistors</i>
>0	Q2, Q4, Q5, Q18, Q20
<0	Q9, Q19, Q20
Bipolar	Q16



Laser Probing : some results

Buried depth (μm) [Ref. 2] laser	Sensitive transistors (laser mapping Ref. 2)
10-15	Q9/Q14, Q20
40-45	Q4/Q5, Q8/Q10 et Q15
100	Q2/Q3/Q4

Ref. 2 – C. Weulersse et al., “Probing SET Sensitive Volume in Linear Devices Using Focused Laser Beam at different wavelength”, presented at RADECS 2007, Deauville (France), 10-14 September 2007.



Heavy ion probing : irradiation conditions

*Tandem Van de
Graaff IPN
(Orsay)*

*Synchrotron
GANIL
(Caen)*

Ion species	E (MeV) Min/max	LET (MeV/mg.cm ²) Max/min	Range (μm) Min/max
Br	25	22.8	7.5
	80	35	15.4
Ni	52	28	13
	210	29.5	35
Xe (E ₀ =35MeV/n)	500	64	38
	6000	26	708

*High LET
("Sat.")*

*Broad
range*

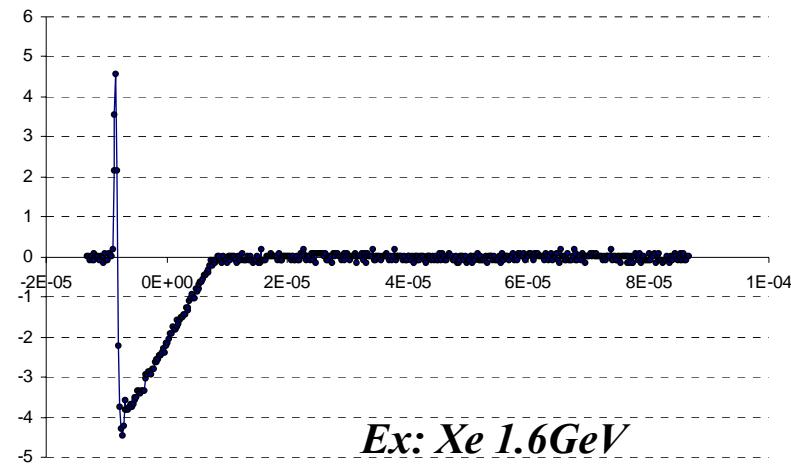
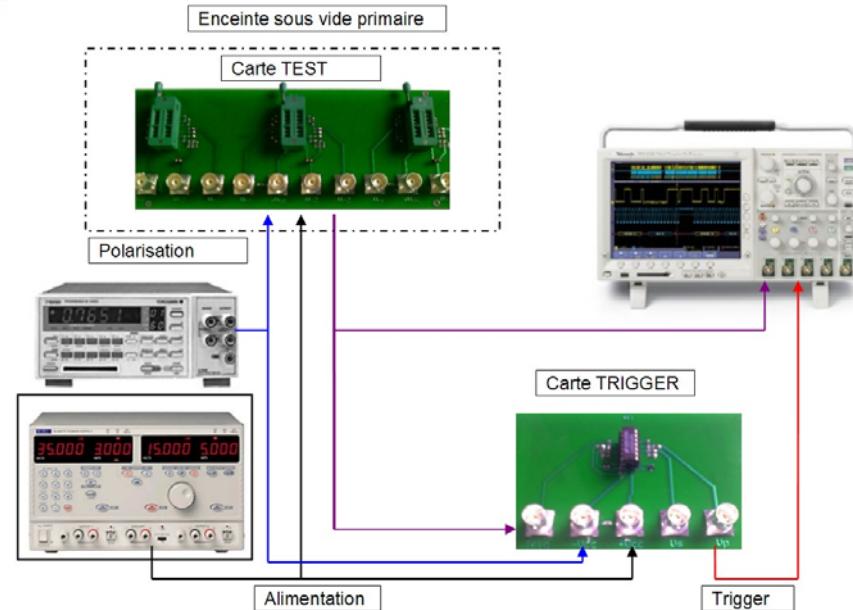
IPN => under vacuum, Ganil => in the air

LET and range adjustment:

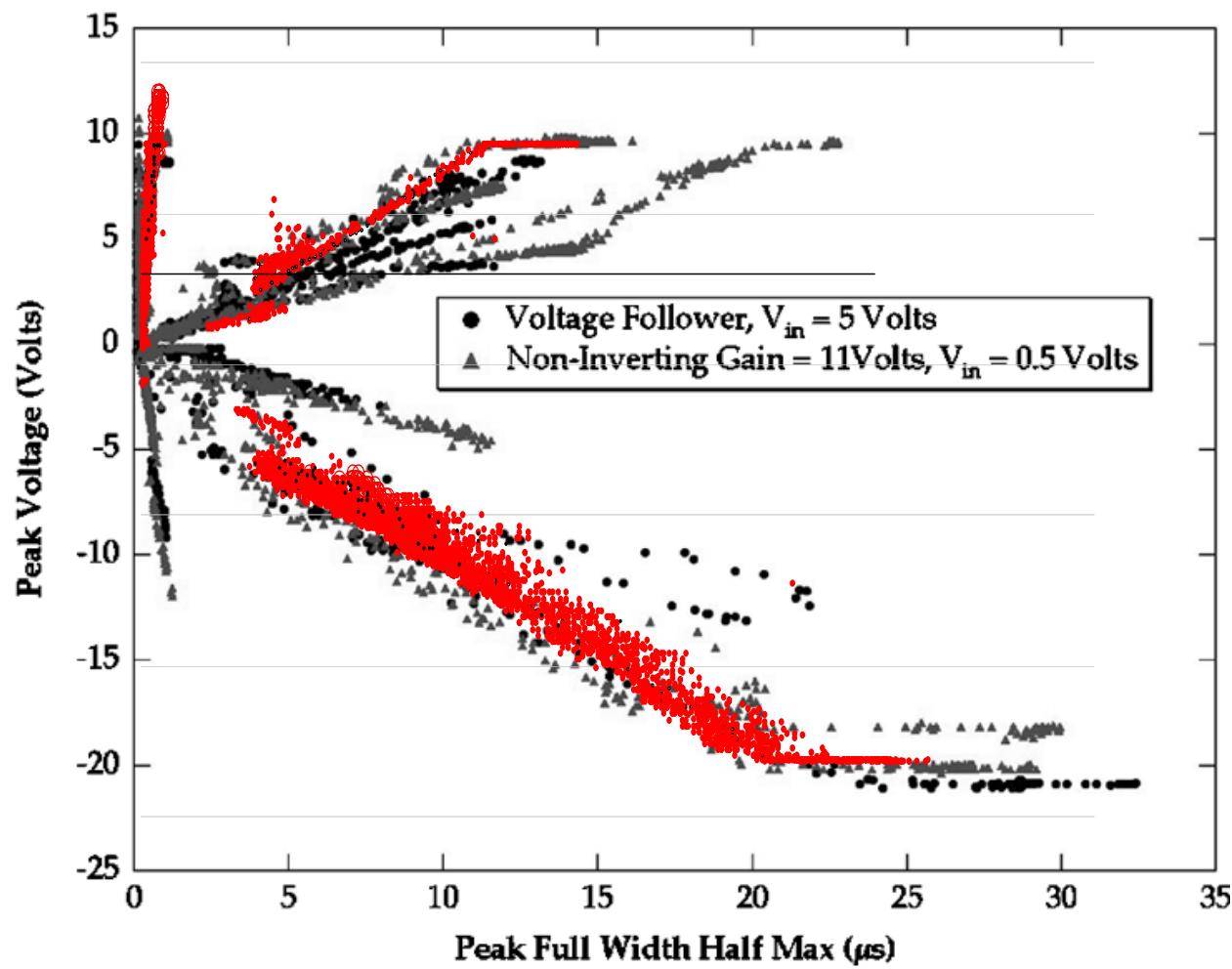
- *IPN: acceleration voltage*
- *GANIL : combination of air & aluminum foils*

Experimental set-up and test conditions

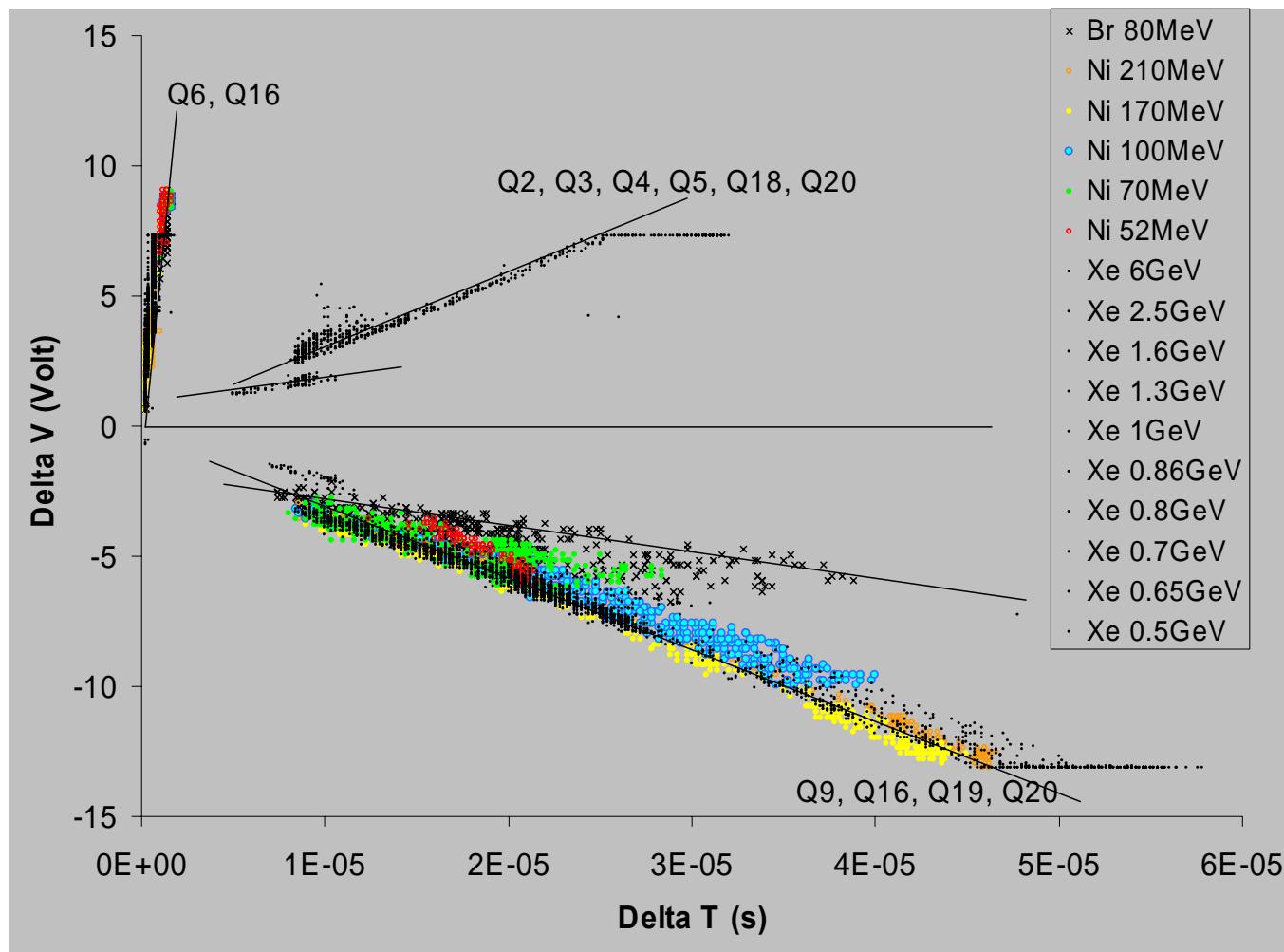
- bipolar bias ($V_{cc}=\pm 15V$)
- non-inverter conf. with gain x2 and $V_{in}=10V$
- coax. probe $\approx 1m$ long (slightly different configurations at IPN (test under vacuum => feedthrough) and Ganil (in air))
- SETs captured by digital oscilloscope on threshold detection (500mV)
- VB macro to extract amplitude/duration characteristics and construct $dV(dT)$ plots
- 500 events max to limit TiD degradation (WC=7krad)



ΔV vs ΔT plots



ΔV vs ΔT plots : IPN and Ganil



SET count vs range of ions

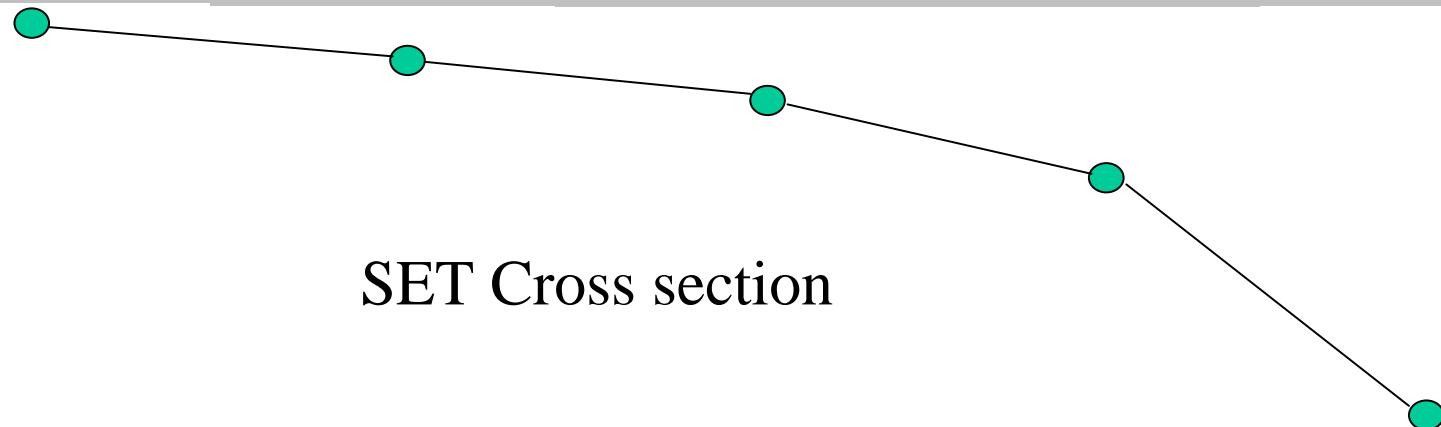
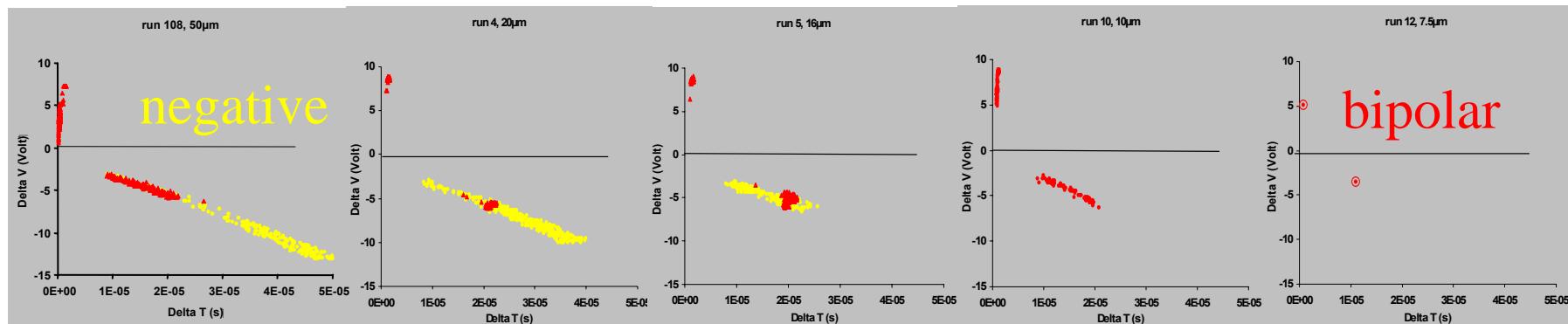
Xe 650MeV
50 µm

Ni 100MeV
20 µm

Ni 70MeV
16 µm

Br 40MeV
10 µm

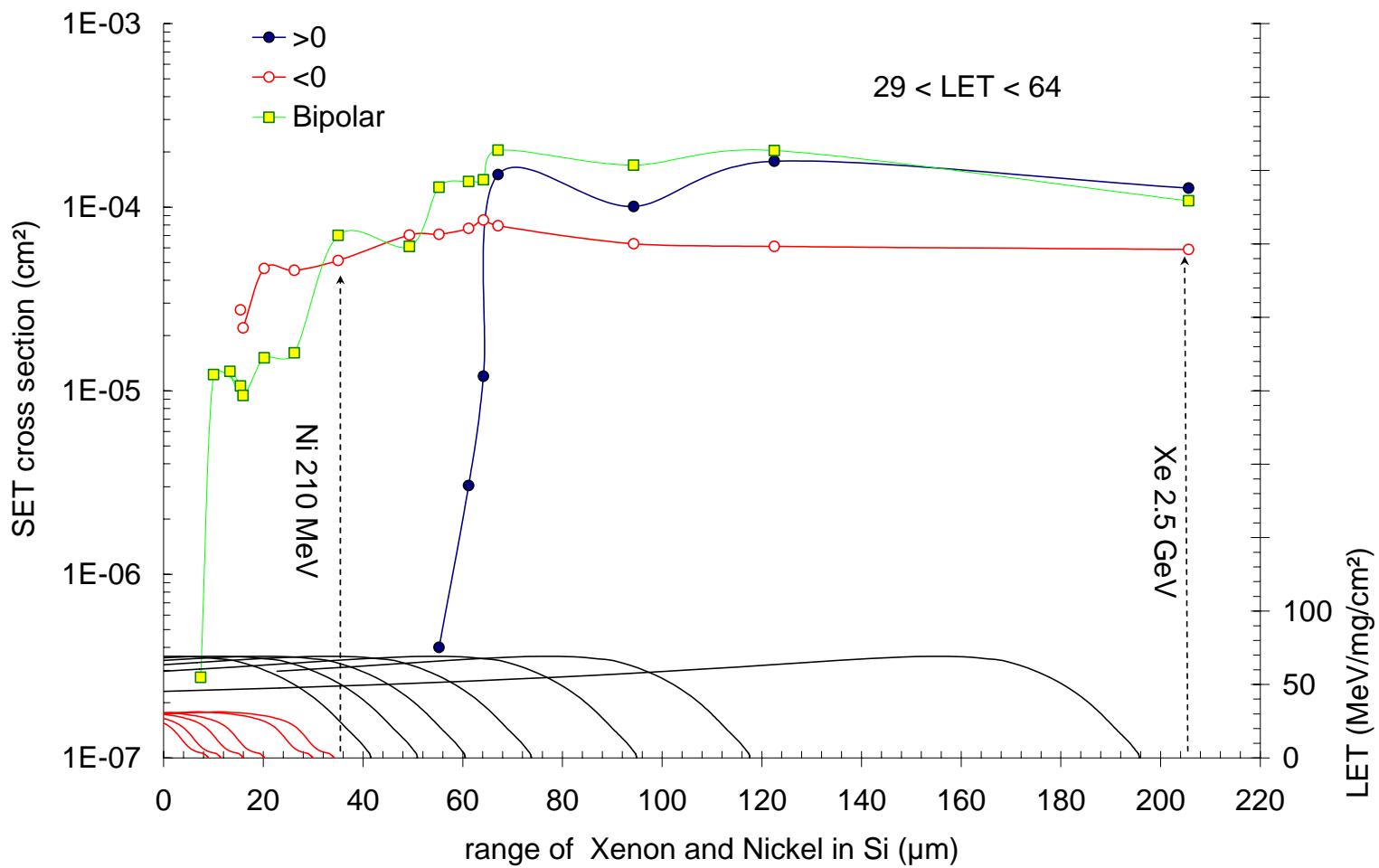
Br 25MeV
7.5 µm



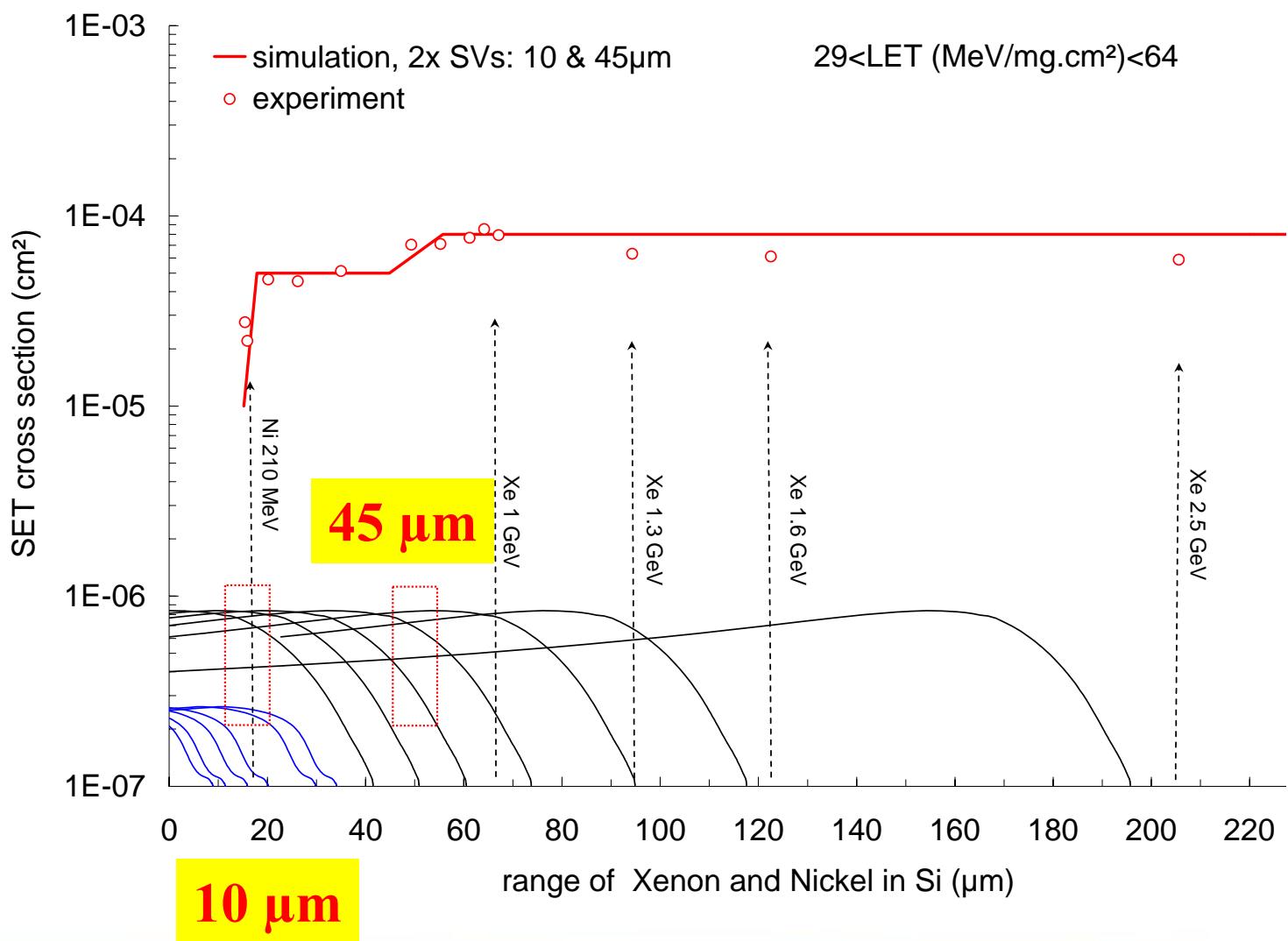
$$LET \approx cst.$$



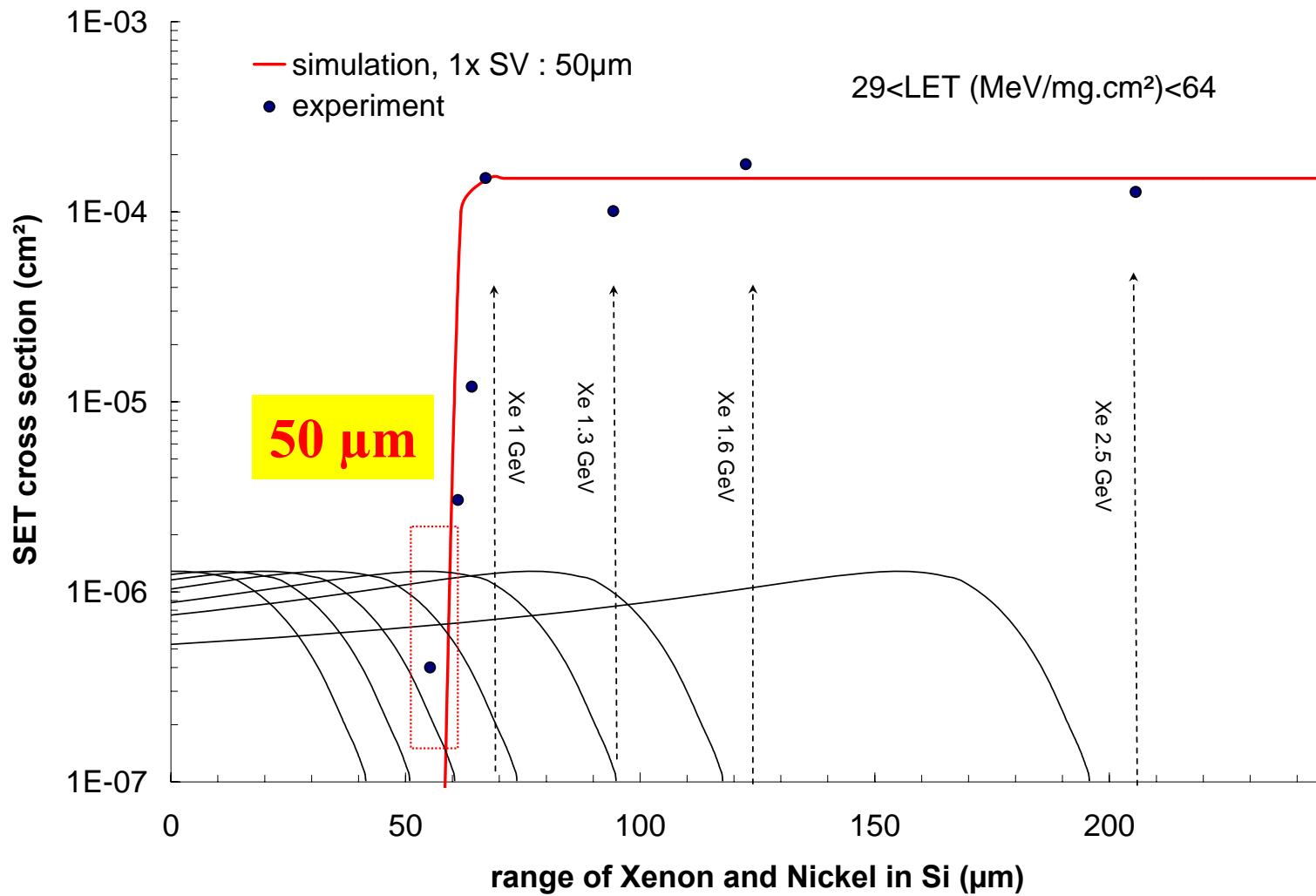
Evolution of measured cross-section with range



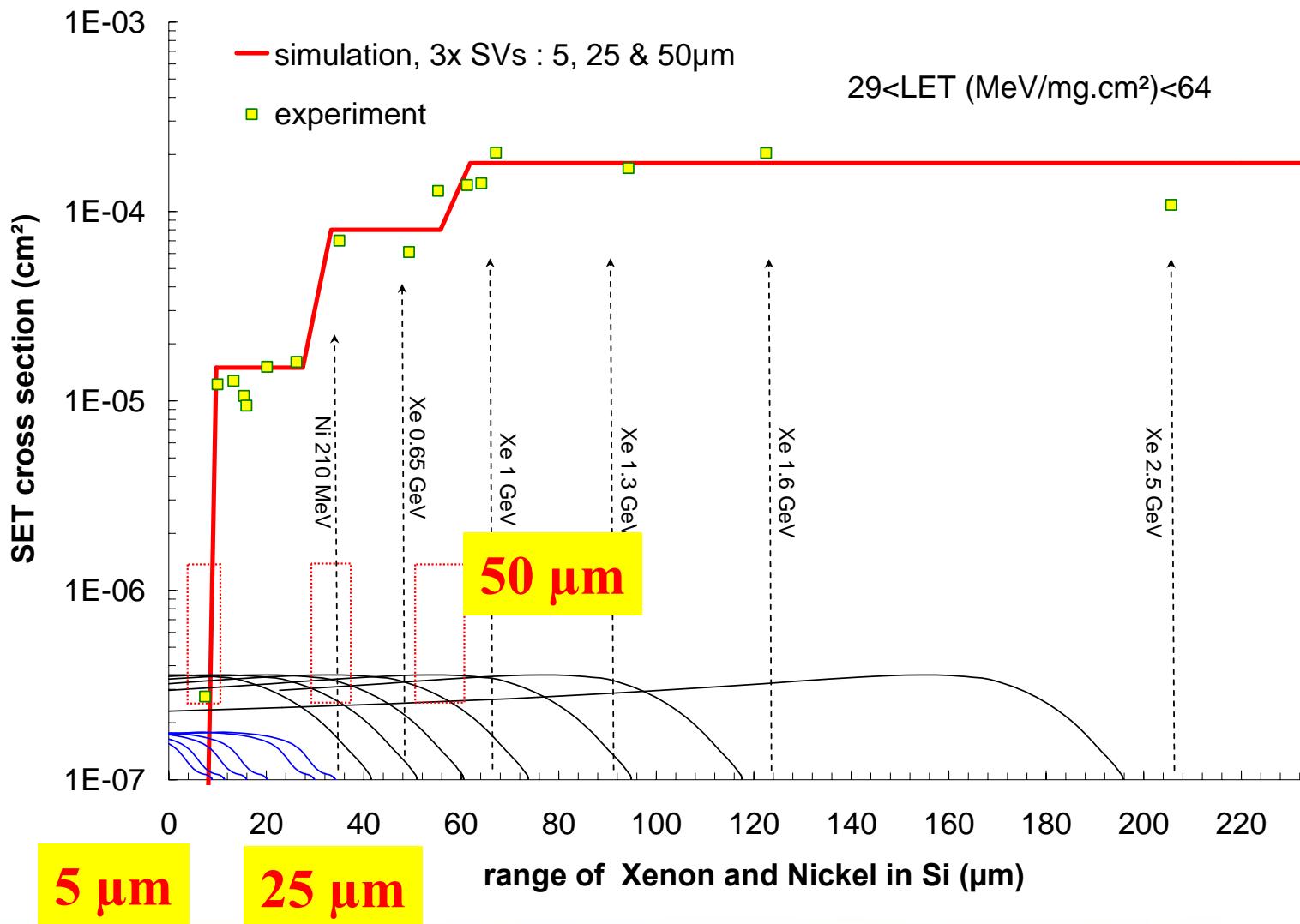
Correlation measurement/RPP calculations: SET<0



Correlation measurement/RPP calculations: SET>0



Correlation measurement/RPP calculations: Bip. SETs



Correlation laser/heavy ion data : sensitive depths

<i>SET</i>	<i>Laser Depth (in μm) [Ref. 2]</i>	<i>Heavy ion depth: RPP calculations (in μm)</i>	<i>X-section ($\text{cm}^2/\text{dev.}$)</i>
>0	15	/	
	40	50	$1.5 \ 10^{-4}$
	100	/	
<0	10	10	$5 \ 10^{-5}$
	45	45	$8 \ 10^{-5}$
bipolar	Not measured	5	$1.5 \ 10^{-5}$
		25	$8 \ 10^{-5}$
		50	$2 \ 10^{-4}$

Conclusions

- The overall laser/heavy ion data correlate quite well
- By this work, it was confirmed that the laser technique can be used for probing device SET sensitivities and measure sensitive depths in order to help defining the appropriate geometrical parameters for prediction
- The heavy ion data also provide important insight on the test procedures to be applied for SET testing and x-section measurements. It has been shown that the main SET types could be triggered even with low range beams (down to about 15 μ m). However, beam ranges much **greater than 50 μ m** have to be used for characterization purpose and defining worst case conditions.